TOSHIBA Intelligent Power Module Silicon N Channel IGBT

MIG400J101H

High Power Switching Applications Motor Control Applications

- Integrates inverter power circuits & control circuits (IGBT drive units, protection units for over-current, under-voltage & over temperature) in one package.
- The electrodes are isolated from case.

High speed type IGBT : V_{CE} (sat) = 2.5V (max)

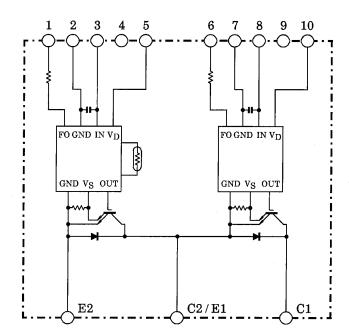
 $t_{off} = 2.0 \mu s \text{ (max)}$

 $t_{rr} = 0.15\mu s \text{ (max)}$

: TOSHIBA 2-121A1A Package dimensions

Weight: 510g

Equivalent Circuit



- 1. FO (L)
- 2. GND (L)
- 3. IN (L)
- 4. Open
- $\begin{array}{cc} 5. \ \mathrm{V_D} \ (\mathrm{L}) \\ 10.\mathrm{V_D} \ (\mathrm{H}) \end{array}$

- 6. FO (H)
- 7. GND (H)
- 8. IN (H)
- 9. Open

1 2002-12-06



Maximum Ratings $(T_j = 25^{\circ}C)$

Stage	Characteristic	Condition	Condition Symbol		Unit
Inverter	Supply voltage	P-N power terminal	Vcc	450	V
	Collector-emitter voltage	_	V _{CES}	600	V
	Collector current	Tc = 25°C, DC	IC	400	Α
	Forward current	Tc = 25°C, DC	I _F	400	Α
	Collector power dissipation	Tc = 25°C	PC	1600	W
	Junction temperature	_	Tj	150	°C
	Control supply voltage	V _D -GND terminal	V _D	20	V
Control	Input voltage	IN-GND terminal	V _{IN}	20	V
Control	Fault output voltage	FO-GND (L) terminal	V _{FO}	20	V
	Fault output current	FO sink current	I _{FO}	14	mA
	Operating temperature	_	T _C	-20 ~ +100	°C
Module	Storage temperature range	_	T _{stg}	-40 ~ +125	°C
	Isolation voltage	AC 1 minute,	V _{ISO}	2500	V
	Screw torque	M6	_	3	Nm

Electrical Characteristics ($T_j = 25^{\circ}C$)

a. Inverter Stage

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Collector cut-off current	losy	$V_{CE} = 600V$	T _j = 25°C	_	_	2	mA
Collector cut-on current	ICEX		T _j = 125°C	_	_	40	
Collector-emitter saturation voltage	V	V_D = 15V, I_C = 400A V_{IN} = 3V \rightarrow 0V	T _j = 25°C	_	2.0	2.5	V
Collector-entitler saturation voltage	VCE (sat)		T _j = 125°C	_	2.0	_	
Forward voltage	V _F	I _F = 400A		_	2.1	2.7	V
	t _{on}	V_{CC} = 300V, I_{C} = 400A V_{D} = 15V, V_{IN} = 3V \leftrightarrow 0V Inductive load		1.4	2.1	2.8	μs
	t _{c (on)}			_	1.2	1.8	
Switching time	t _{rr}			_	0.08	0.15	
	t _{off}		(Note 1)	_	1.2	2.0	
	t _{c (off)}			_	0.3	0.6	

b. Control Stage $(T_j = 25^{\circ}C)$

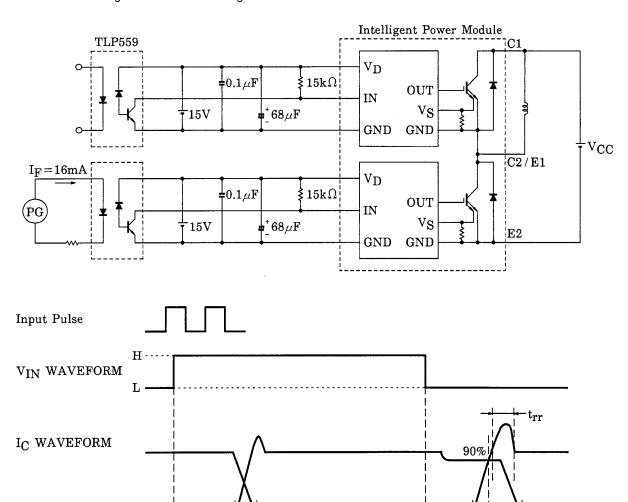
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Control circuit current		I _D	V _D = 15V	_	20	30	mA
Input on signal voltage		V _{IN (on)}	V _D = 15V, I _C = 400mA	0.9	1.1	1.3	V
Fault output current	Protection	I _{FO (on)}	- V _D = 15V	8	10	12	mA
	Normal	I _{FO (off)}		_	_	1	
Over current protection trip level		ОС	V _D = 15V, T _j = 125°C	560	640	_	Α
Short circuit protection trip level		SC	V _D = 15V, T _j = 125°C	840	960	_	Α
Over current cut-off time		t _{off (OC)}	V _D = 15V	_	10	_	μs
Over	Trip level	ОТ	0	111	118	125	°C
temperature protection	Reset level	OTr	Case temperature	93	100	107	
Control supply under voltage protection	Trip level	UV		11.3	12.0	12.7	.,
	Reset level	UVr	_	11.8	12.5	13.2	V
Fault output pulse width		t _{FO}	V _D = 15V	1	2	3	ms

c. Thermal Resistance $(T_j = 25^{\circ}C)$

Characteristic	Symbol	Test Condition	MIN	TYP.	MAX	Unit
Junction to case thermal	D., 4	IGBT	_	_	0.078	°C/W
resistance	R _{th (j-c)}	FRD	_	_	0.208	
Case to fin thermal resistance	R _{th (c-f)}	Compound is applied	_	0.05	_	°C/W

Note 1: Switching time test circuit & timing chart

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10%

 $t_{
m off}$

10%

tc (off)

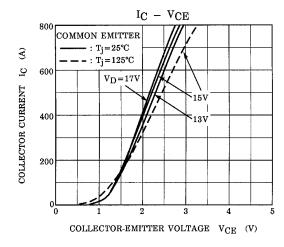
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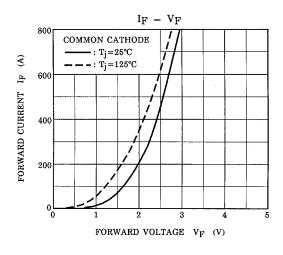
 t_{on}

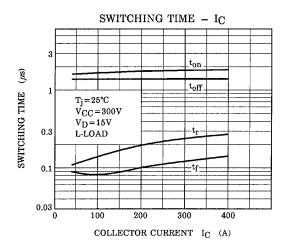
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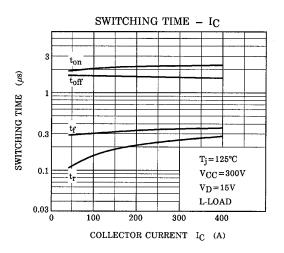
t_c(on)

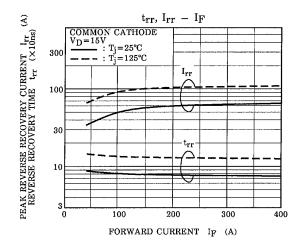
V_{CE} WAVEFORM

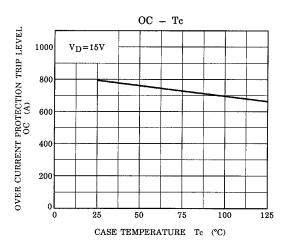


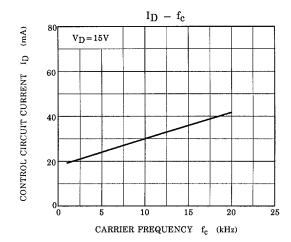


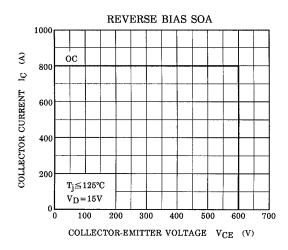


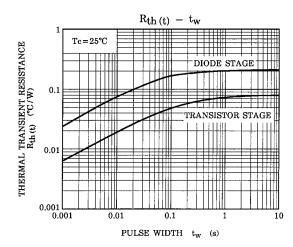






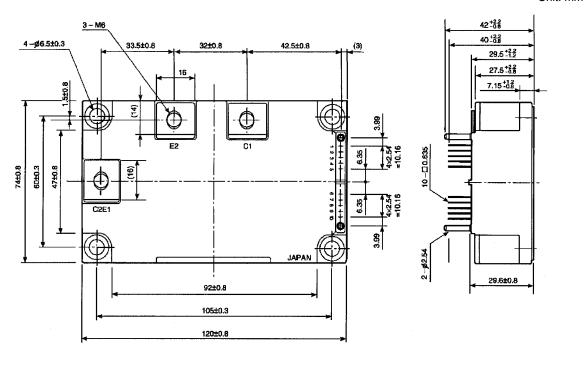


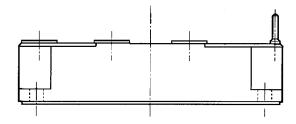




Package Dimensions: TOSHIBA 2-121A1A

Unit: mm





- 1. FO (L)
- 2. GND (L)
- 3. IN (L)
- 4. Open
- 5. V_D (L)

- 6. FO (H) 7. GND (H) 8
 - 8. IN (H)
- 9. Open
- 10.V_D (H)

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